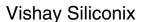
COMPLIANT HALOGEN

FREE





Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)						
- 20	$0.054 \text{ at V}_{GS} = -4.5 \text{ V}$	- 4.5 ^a							
	0.070 at V _{GS} = - 2.5 V	- 4.5 ^a	9.5 nC						
	0.104 at V _{GS} = - 1.8 V	- 4.5 ^a	9.5110						
	0.165 at V _{GS} = - 1.5 V	- 1.5							

PowerPAK SC-70-6 Dual

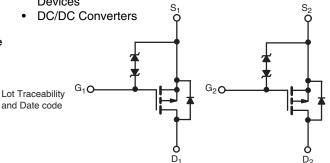
2.05 mm

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2500 V
- 100 % R_q Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Charger Switches and Load Switches for Portable Devices



Ordering Information: SiA923EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

2.05 mm

P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	S T _A = 25 °C, unles	ss otherwise note	ed			
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 20	V		
Gate-Source Voltage		V _{GS}	± 8	v		
Continuous Drain Current (T, = 150 °C)	$T_C = 25 \degree C$ $T_C = 70 \degree C$. I _D	- 4.5 ^a - 4.5 ^a			
(·j	$T_A = 25 ^{\circ}\text{C}$ $T_A = 70 ^{\circ}\text{C}$		- 4.5 ^{a, b, c} - 4.5 ^{a, b, c}	Α		
Pulsed Drain Current		I _{DM}	- 15			
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	- 4.5 ^a - 1.6 ^{b, c}			
Maximum Power Dissipation	$T_C = 25 ^{\circ}\text{C}$ $T_C = 70 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$	P _D	7.8 5 1.9 ^{b, c}	w		
Operating Junction and Storage Temperature Ra	T _A = 70 °C	T _J , T _{stg}	1.2 ^{b, c} - 55 to 150			
Soldering Recommendations (Peak Temperature	v	o. sig	260	°C		

Marking Code

 $X \times X$

Part # code

THERMAL RESISTANCE RATINGS								
Parameter	Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R_{thJA}	52	65	°C/W			
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16				

Notes

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.

SiA923EDJ

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static	1 v	V 0.V I 050 A		1	I	I .,			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V			
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 15		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.5					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.5		- 1.4	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 0.3	± 3	- - μΑ			
<u> </u>	400	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		± 3	± 30				
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1				
	Doo	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, $V_{GS} =$ - 4.5 V	- 15			Α			
		V _{GS} = - 4.5 V, I _D = - 3.8 A		0.044	0.054				
Durin O	B	V _{GS} = - 2.5 V, I _D = - 3.3 A		0.057	0.070				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 1 A		0.075	0.104	Ω			
		V _{GS} = - 1.5 V, I _D = - 0.5 A		0.097	0.165				
Forward Transconductancea	9 _{fs}	V _{DS} = - 10 V, I _D = - 3.8 A		11		S			
Dynamic ^b					l				
·		V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 4.9 A		16.3	25	nC			
Total Gate Charge	Qg			9.5	14.5				
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 4.9 A		1.4					
Gate-Drain Charge	Q _{gd}			2.3					
Gate Resistance	R _g	f = 1 MHz	1	5.1	10	Ω			
Turn-On Delay Time	t _{d(on)}			15	25				
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 2.6 \Omega$		16	25				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.9 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_q = 1 \Omega$		30	45				
Fall Time	t _f	-		10	15	1			
Turn-On Delay Time	t _{d(on)}			7	15	ns			
Rise Time	t _r	V_{DD} = - 10 V, R_{L} = 2.6 Ω		12	20	1			
Turn-Off Delay Time	t _{d(off)}			26	40	1			
Fall Time	t _f	<u>~ ~ ~ </u>		10	15	1			
Drain-Source Body Diode Characterist									
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	- 4.5						
Pulse Diode Forward Current	I _{SM}	, , ,			- 15	A			
Body Diode Voltage	V _{SD}	I _S = - 3.9 A, V _{GS} = 0 V		- 0.9	- 1.2	V			
Body Diode Reverse Recovery Time	t _{rr}	<i>y</i> 40 -		13	25	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	1		5.5	12	nC			
Reverse Recovery Fall Time	t _a	$I_F = -3.9 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 ^{\circ}\text{C}$		7.5	1.2	- ns			
Reverse Recovery Rise Time	t _b	1		5.5					
- Tovorso Hecovery Hise Hille	ď			5.5					

Notes:

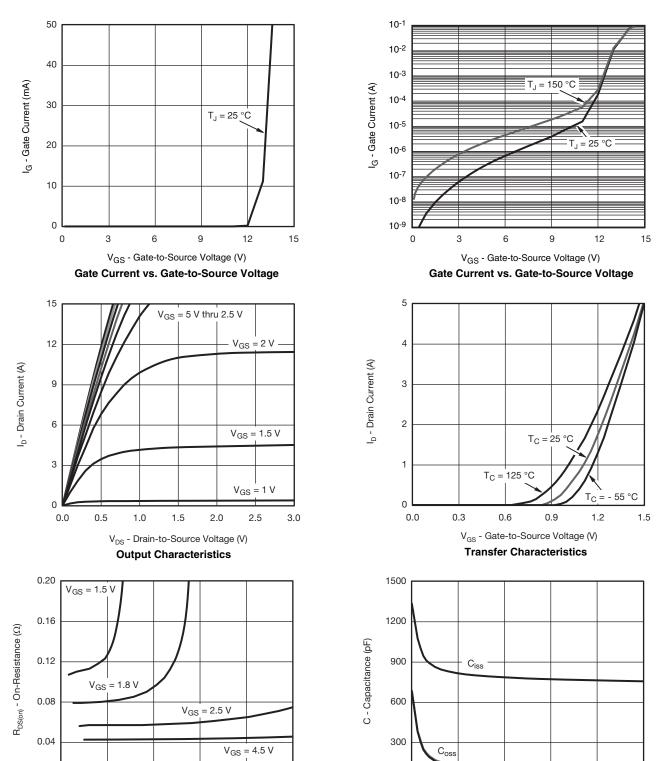
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



I_D - Drain Current (A)

On-Resistance vs. Drain Current and Gate Voltage

6

9

12

0

0

8

12

V_{DS} - Drain-to-Source Voltage (V)

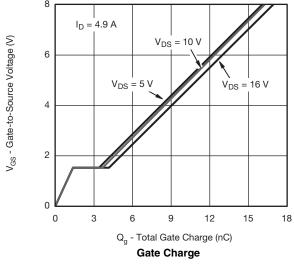
Capacitance

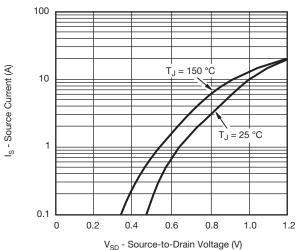
20

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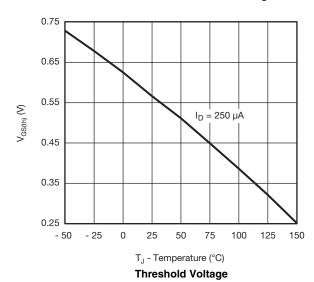
VISHAY

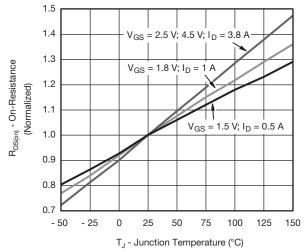
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



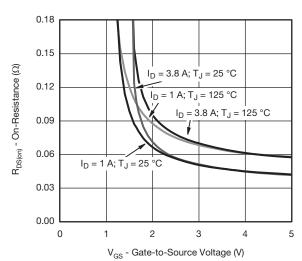




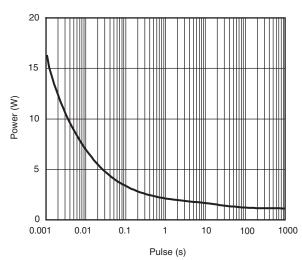




On-Resistance vs. Junction Temperature



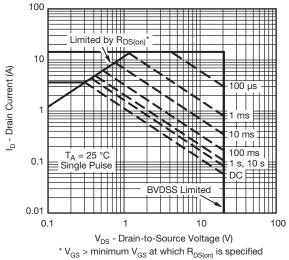
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

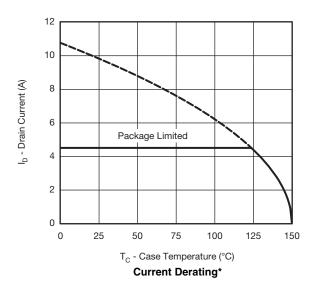


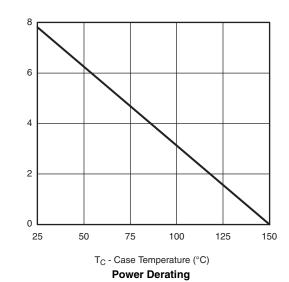
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Safe Operating Area, Junction-to-Ambient

Power Dissipation (W)



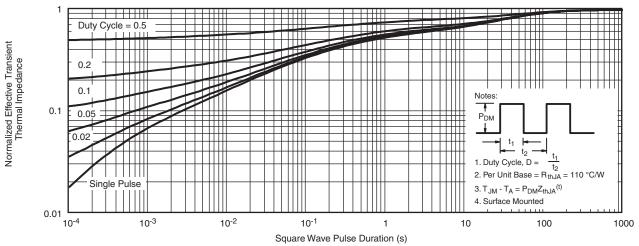


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

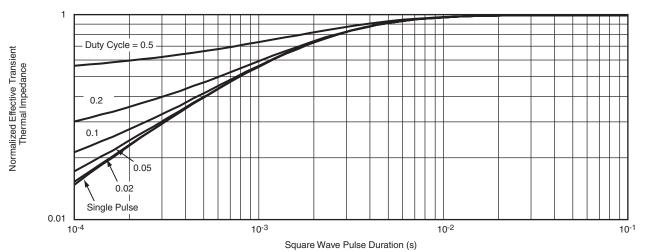
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

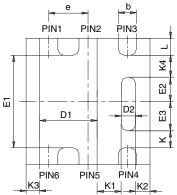
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?66803.

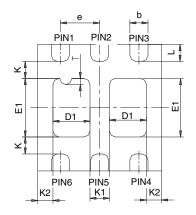




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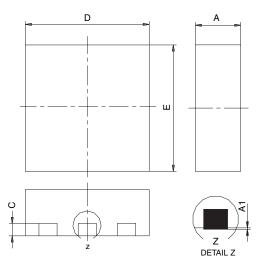
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD							DUAL PAD				
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP		0.011 TYP		0.275 TYP		0.011 TYP				
K1		0.400 TYP		0.016 TYP		0.320 TYP		0.013 TYP				
K2		0.240 TYP		0.009 TYP		0.252 TYP		0.010 TYP				
К3		0.225 TYP		0.009 TYP					•	•		
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

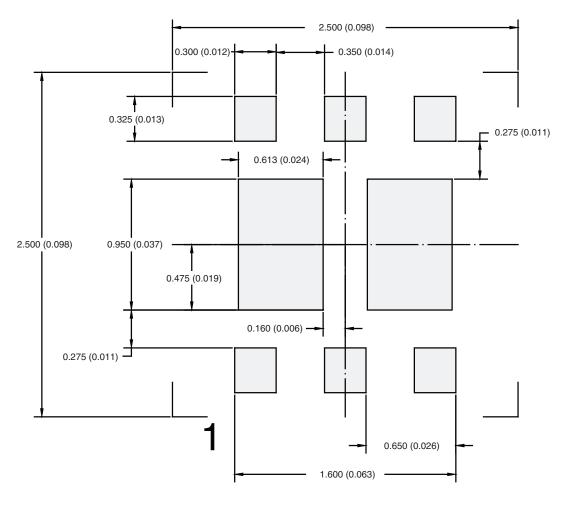
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

Return to Index



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